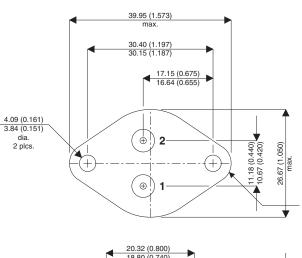
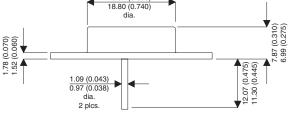


Dimensions in mm (inches)





N-CHANNEL POWER MOSFET

V _{DSS}	400V
I _{D(cont)}	14A
R _{DS(on)}	0.300Ω

FEATURES

- REPETITIVE AVALANCHE RATINGS
- DYNAMIC DV/DT RATING
- HERMETICALL SEALED
- SIMPLE DRIVE REQUIREMENTS
- EASE OF PARALLELING

TO-3 (TO-204AA) Metal Package

Pin 2 - Gate Case - Drain

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V _{GS}	Gate – Source Voltage	0000	±20V	
I _D	Continuous Drain Current	$(V_{GS} = 0, T_{case} = 25^{\circ}C)$	14A	
		$(V_{GS} = 0, T_{case} = 100^{\circ}C)$	9.0A	
I _{DM}	Pulsed Drain Current ¹	56A		
P _D	Power Dissipation @ T _{case} = 25°C		150W	
	Linear Derating Factor	1.2W/°C		
E _{AS}	Single Pulse Avalanche Energy	11.3mJ		
I _{AR}	Avalanche Current ¹	14A		
E _{AR}	Repetitive Avalanche Energy ¹		15mJ	
dv/dt	Peak Diode Recovery ⁴		4.0V/ns	
T _J , T _{stg}	Operating and Storage Temperature Range		-55 to +150°C	

Notes

Pin 1 – Source

1) Pulse Width \leq 300µs, Duty Cycle \leq 2%

2) Repetitive Rating – Pulse width limited by maximum junction temperature.

3) $V_{DD} = 50V$, Peak I_L = 14A, Starting T_J = 25°C

4) $I_{SD} \le 14A$, di/dt $\le \overline{1}45A/\mu s$, $V_{DD} \le 400V$, $T_J \le 150^{\circ}C$, Suggested $R_G = 2.35\Omega$

Semelab PIc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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IRF350 2N6768



IRF350 2N6768

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test Cond	ditions	Min.	Тур.	Max.	Unit
	STATIC ELECTRICAL RATINGS	•		•			•
BV _{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V$	I _D = 1mA	400			V
ΔBV_{DSS}	Temperature Coefficient of	Reference to 25°C			0.46		V/°C
ΔT_{J}	Breakdown Voltage	I _D = 1mA			0.40		
R _{DS(on)}	Static Drain – Source On–State	V _{GS} = 10V	I _D = 9.0A			0.300	
	Resistance	V _{GS} = 10V	I _D = 14A			0.400	Ω
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$	I _D = 250μA	2.0		4.0	V
9 _{fs}	Forward Transconductance	$V_{DS} \ge 15V$	I _{DS} = 9.0A	6.0			S (ひ)
IDSS	Zero Gate Voltage Drain Current	$V_{GS} = 0V$	V _{DS} = 320V			25	- μΑ
			T _J = 125°C			250	
I _{GSS}	Gate – Source Leakage Forward	$V_{GS} = +20V$				+100	n۸
I _{GSS}	Gate – Source Leakage Reverse	$V_{GS} = -20V$				-100	nA
	DYNAMIC CHARACTERISTICS	•					
C _{iss}	Input Capacitance	$V_{GS} = 0V$			2660		
C _{oss}	Output Capacitance	V _{DS} = 25V			680		pF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz			250		
Qg	Total Gate Charge	V _{GS} = 10V		52		110	
Q _{gs}	Gate – Source Charge	I _D = 14A		5.0		18	nC
Q _{gd}	Gate – Drain ("Miller") Charge	V _{DS} = 200V		25		65	
t _{d(on)}	Turn-On Delay Time	V _{DD} = 200V				35	
t _r	Rise Time	I _D = 14A				190	– ns
t _{d(off)}	Turn–Off Delay Time	R _G = 2.35Ω				170	
t _f	Fall Time					130	
	SOURCE – DRAIN DIODE CHARAC	TERISTICS					•
I _S	Continuous Source Current					14	A
I _{SM}	Pulse Source Current ²					56	
V _{SD}	Diode Forward Voltage ¹	$I_S = 28A$ $V_{GS} = 0$	$T_J = 25^{\circ}C$			1.7	V
t	Reverse Recovery Time	$I_F = 28A$	T _{.1} = 25°C			1200	ns
u _{rr} Q _{rr}	Reverse Recovery Charge ¹	$d_i / d_t \le 100 \text{ A}/\mu$	e e			250	μC
t _{on}	Forward Turn–On Time				Negligible		•
	PACKAGE CHARACTERISTICS				-33		
L _{D +} L _S	Total Inductance (measured from the centre of drain pad to center of source pad)			6.1		nH	
	THERMAL CHARACTERISTICS			1			1
R _{thJC}	Thermal Resistance Junction – Case	•				0.83	3
R _{thJA}	Thermal Resistance Junction – Ambi				30	− °C/W	

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